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SIDDHARTH INSTITUTE OF ENGINEERING & TECHNOLOGY:: PUTTUR
(AUTONOMOUS)**B.Tech II Year I Semester Supplementary Examinations August-2022****BASIC ELECTRONIC DEVICES**

(Common to EEE & ECE)

Time: 3 hours

Max. Marks: 60

(Answer all Five Units 5 x 12 = 60 Marks)

UNIT-I

- 1 a Explain Drift and Diffusion current for a semiconductor. L2 6M
b With expressions, explain mobility and conductivity of a semiconductor. L2 6M

OR

- 2 a Describe the Temperature Dependence of PN Junction Diode on VI Characteristics. L1 6M
b How does the reverse saturation current of PN junction diode varies with temperature? Explain. L2 6M

UNIT-II

- 3 a Draw and explain the basic structure of LED. Mention the applications of LED. L2 6M
b Write notes on Liquid Crystal Display. L2 6M

OR

- 4 a Draw the basic structure of an SCR. Explain its characteristics and list the applications. L1 6M
b Define Holding Current and Latching Current of SCR. L2 6M

UNIT-III

- 5 Derive the expression for ripple factor of inductor filter. Mention the need of Bleeder resistor. L1 12M

OR

- 6 a With neat diagram, explain Bridge Rectifier. L2 6M
b Discuss the L Section Filter with neat diagram. L2 6M

UNIT-IV

- 7 a Give the current components of PNP transistor and explain. L2 8M
b With reference to BJT, explain the following terms Emitter Efficiency, Base Transportation Factor and Large signal current gain. L1 4M

OR

- 8 a Explain the construction and principle of operation of N-channel JFET. L2 6M
b Define the JFET Volt-Ampere Characteristics and determine FET parameters. L1 6M

UNIT-V

- 9 a Explain the concept of DC and AC Load lines and discuss the criteria for fixing the Q-point. L2 6M
b Mention different types of Biasing a Transistor. And explain the Fixed Bias of a Transistor in detail. L2 6M

OR

- 10 a Derive the stability factors S, S' and S'' of a Transistor Voltage Divider bias . L3 6M
b Mention the advantages and disadvantages of various biasing techniques of BJT. L2 6M

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